

#### ABSTRACT OF THE DISCLOSURE

The invention realizes, in a semiconductor device including n-channel field-effect transistors and p-channel field-effect transistors in which a channel direction is parallel to a  $\langle 100 \rangle$  axis, a semiconductor device having excellent drain current characteristics of both n-channel field-effect transistors and p-channel field-effect transistors. In a semiconductor device including n-channel field-effect transistors N1 and N2 and p-channel field-effect transistors P1 and P2, a stress control film 209 that covers the gate electrodes of the n-channel and p-channel field-effect transistors from upper surfaces thereof is not formed or is made thin above shallow trench isolations adjacent to active regions formed by the p-channel field-effect transistors P1 and P2 in a case where the stress control film 209 is tensile film stress. Thus, improvement of drain currents of both the n-channel and p-channel transistors can be expected. For this reason, it is possible to improve overall characteristics.